风光欣技术资料

9015

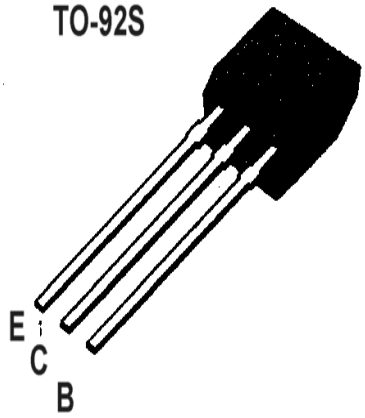
PNP Transistors

—PNP Silicon—

■■ **APPLICATION：** General Purpose Applications.

■■ **MAXIMUM RATINGS**（Ta=25℃）

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V_{CBO}	-50	V
Collector-emitter voltage	V_{CEO}	-40	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-0.1	A
Collector Power Dissipation	P_C	0.3	W
Junction Temperature	Tj	150	℃
Storage Temperature Range	Tstg	-55~150	℃



■■**ELECTRICAL CHARACTERISTICS**

（Ta=25℃）

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
Collector-Base Breakdown Voltage	BV_{CBO}	-50			V	I_C=-0.1mA I_E=0
Collector-Emitter Breakdown Voltage	BV_{CEO}	-40			V	I_C=-1mA I_B=0
Emitter-Base Breakdown Voltage	BV_{EBO}	-5			V	I_E=-0.1mA I_C=0
Collector Cut-off Current	I_{CBO}			-0.1	uA	V_{CB}=-50V I_E=0
Emitter Cut-off Current	I_{EBO}			-0.1	uA	V_{EB}=-5V I_C=0
Base-Emitter Voltage	$V_{BE(on)}$			-0.8	V	V_{CE}=-5V I_C=-2mA
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			-1	V	I_C=-0.1A I_B=-10mA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-0.3	V	I_C=-0.1A I_B=-10mA
DC Current Gain	H_{FE}	60		600	β	V_{CE}=-5V I_C=-1mA
Gain bandwidth product	f_T	100	190		MHz	V_{CE}=-5V I_E=-10mA
Common Base Output Capacitance	Cob		5	7	pF	V_{CB}=-10V I_E=0 f=1MHz
Noise Figure	NF		3	5	dB	V_{CE}=-5V,I_C=-0.2mA, f=10KHz,Rg=1KΩ

■■ **HFE(1)Classification And Marking**

Print Mark	9015		
Classification	A	B	C
HFE	60~150	100~300	200~600